AUXILIARY REQUEST 7

Claims

- marked-up version -

1. A susceptor (1) for mounting a wafer in a CVD apparatus for epitaxially growing a semiconductor coating on the wafer, ~~that~~ the susceptor (1) generate~~s~~ing heat by induction heating~~, the susceptor (1)~~ and comprising:

a graphite base material (1A); and

a ceramic coating layer,

characterized in that

the graphite base material (1A) has a coefficient of thermal expansion of 3.5 × 10^{-6}/K or higher and 4.5 × 10^{-6}/K or lower, an electrical resistivity (ρ_0) of 8.0 μΩ·m or higher and 13.0 μΩ·m or lower, a bulk density of 1.70 to 1.80 g/cm^3 and a flexural strength of 35 to 60 MPa and exhibits a variation (ρ_{max}/ρ_{min}) of an in-plane electrical resistivity distribution at room temperature of 1.00 or higher and 1.05 or lower and a rate of high-temperature change (ρ_{1600}/ρ_{800}) of electrical resistivity at 1600°C to that at 800°C of 1.14 or higher and 1.30 or lower;

wherein, to determine physical property values of the graphite base material, a test piece of 10 × 10 × 50 mm is cut out from an arbitrary location of the graphite base material and the bulk density, the coefficient of thermal expansion, the flexural strength, and the electrical resistivity are measured as follows: